

**Silicon PNP Power Transistor**

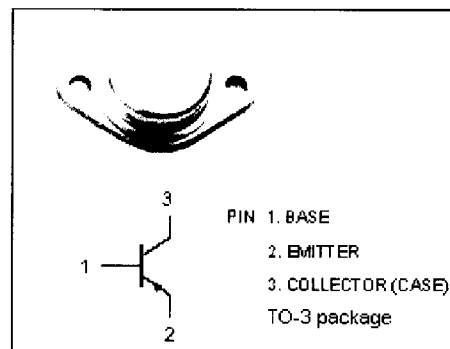
**2SA756**

**DESCRIPTION**

- High Power Dissipation-  
 :  $P_C = 50W(\text{Max.})@T_C=25^\circ\text{C}$
- Collector-Emitter Breakdown Voltage-  
 :  $V_{(BR)CEO} = -80V(\text{Min.})$

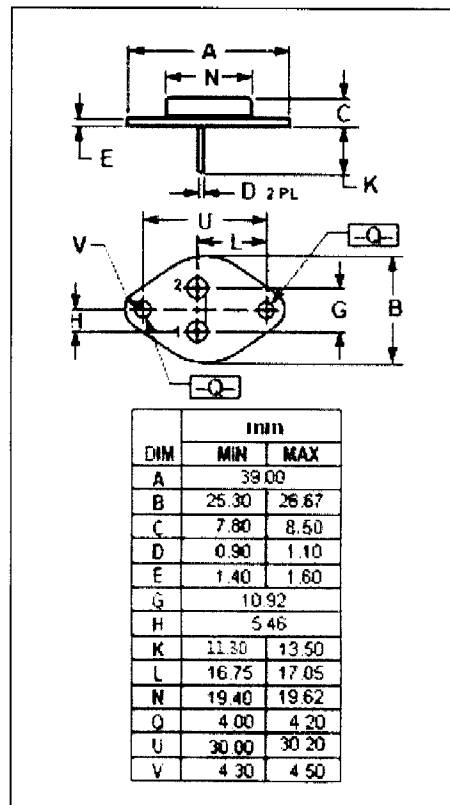
**APPLICATIONS**

- Designed for use in audio amplifier power output stage and general purpose applications.

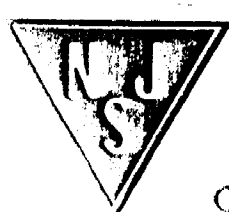


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-100	V
$V_{CEO}$	Collector-Emitter Voltage	-80	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-6	A
$I_{CM}$	Collector Current-Peak	-10	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	50	W
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



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2SA756

## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA; R <sub>BE</sub> = ∞	-80			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -5mA; I <sub>E</sub> = 0	-100			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -5mA; I <sub>C</sub> = 0	-5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -1A			-1.8	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -100V; I <sub>E</sub> = 0			-1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V	25		200	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -5A; V <sub>CE</sub> = -5V	20			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V		20		MHz

### ◆ h<sub>FE-1</sub> Classifications

A	B	C
25-60	50-120	100-200